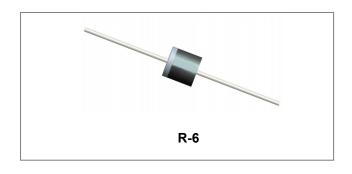






15SQ040L SCHOTTKY BARRIER RECTIFIER



Features

- Super-high speed & low noise switching
- Low voltage drop
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- DC-DC converters
- AC adapter
- · High frequency rectification circuit
- Bypass diodes

Maximum Ratings:

| Characteristics | Symbol | Condition | Max. | Units |
|--|--|--|------|-------|
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | V _{RRM} V _{RWM} V _R | - | 40 | ٧ |
| Average Rectified Forward Current | I _{F (AV)} | 50% duty cycle @T _A = 50°C, rectangular wave form | 15 | Α |
| Peak One Cycle Non-Repetitive Surge Current | I _{FSM} | 8.3 ms, half Sine pulse,T _C = 25°C | 150 | А |

Electrical Characteristics:

| Characteristics | Symbol | Condition | | Тур. | Max. | Units |
|-----------------------|------------------|-----------------------------------|---------|--------|------|-------|
| Forward Voltage Drop* | V_{FM} | I _{FM} =15.0A,Ta=25°0 | C | 0.42 | 0.48 | V |
| Reverse Current* | I _{RM1} | V _{RM} =V _{RRM} | Ta=25℃ | 0.0002 | 0.5 | mA |
| | I _{RM2} | VRM-VRRM | Ta=100℃ | - | 100 | |
| Thermal Resistance | R θJ-c | Between junction and case | | 5 | - | °C/W |
| | R θJ-L | Between junction and lead | | 2.5 | - | |

^{*} Pulse width < 300 µs, duty cycle < 2%



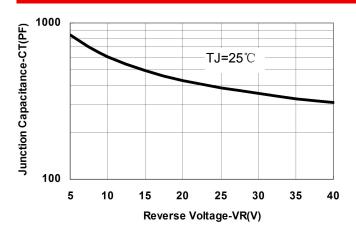




Thermal-Mechanical Specifications:

| Characteristics | Symbol | Condition | Specification | Units | |
|---|------------------|--------------------------|---|-------|--|
| Junction Temperature at reduced reverse voltage at reduced reverse voltage in DC forward mode | TJ | Vr≪80%Vrrm Vr≪50%Vrrm | -55 to +125 -55 to +150 -55 to +200 | °C | |
| Storage Temperature | T _{stg} | - | -55 to +175 | °C | |
| Approximate Weight | wt | - | 2.24 | g | |
| Case Style | | R-6 | | | |

Ratings and Characteristics Curves



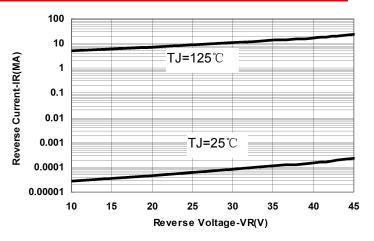


Fig.1-Typical Junction Capacitance Vs.Reverse Voltage

Fig.2-Typical Values Of Reverse Current Vs.Reverse Voltage

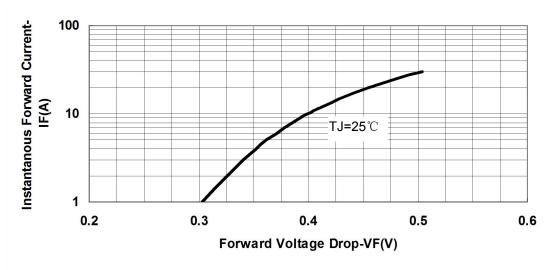


Fig.3-Typical Instantaneous Forward Voltage Characteristics

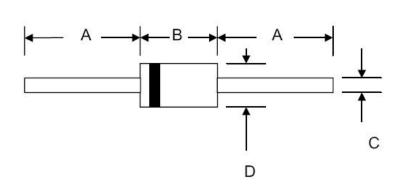
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Mechanical Dimensions R-6



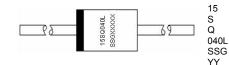
| CVMPOL | Millim | neters | Inc | Inches | | |
|--------|--------|--------|-------|--------|--|--|
| SYMBOL | Min. | Max. | Min. | Max. | | |
| А | 25.4 | - | 1.000 | - | | |
| В | 8.60 | 9.10 | 0.340 | 0.360 | | |
| С | 1.2 | 1.3 | 0.048 | 0.052 | | |
| D | 8.60 | 9.10 | 0.340 | 0.360 | | |

Ordering Information

| Device | Package | Shipping | | |
|----------|--------------|---------------|--|--|
| 15SQ040L | R-6(Pb-Free) | 500pcs / reel | | |

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



Where XXXXX is YYWWL

= Forward Current (15A)

= Package Type= Device Type

= Reverse Voltage (40V) = SSG

= Year

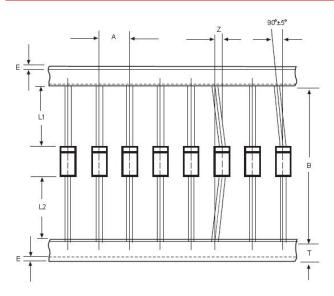
= Year = Week

= Week

WW

= Lot Number

Carrier Tape Specification R-6



| SYMBOL | Millimeters | | | |
|---------|-------------|-------|--|--|
| | Min. | Max. | | |
| Α | 9.50 | 10.50 | | |
| В | 50.9 | 53.9 | | |
| Z | - | 1.20 | | |
| Т | 5.60 | 6.40 | | |
| E | - | 0.80 | | |
| IL1-L2I | - | 1.0 | | |

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